

# Yu-Long Jiang

## List of Publications by Year in descending order

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#	ARTICLE	IF	CITATIONS
1	Significant Performance Improvement of MicroRNA-375 Detection by Modulation of Au Nanoparticle Distribution Using Silicon-on-Insulator MOSFET. IEEE Electron Device Letters, 2022, 43, 128-130.	3.9	3
2	DDDMOSFET Performance Improvement by Gate Oxide Removal Followed by Silicided Source/Drain Formation in Gate Slots. IEEE Transactions on Electron Devices, 2022, 69, 5368-5372.	3.0	0
3	A Novel One-Transistor Active Pixel Sensor With Tunable Sensitivity. IEEE Electron Device Letters, 2021, 42, 927-930.	3.9	6
4	Difference Between Atomic Layer Deposition TiAl and Physical Vapor Deposition TiAl in Threshold Voltage Tuning for Metal Gated NMOSFETs. IEEE Electron Device Letters, 2021, 42, 1830-1833.	3.9	7
5	Ultra-Low Contact Resistivity of $\sim 0.1\text{-}\Omega\cdot\text{mm}$ for Au-Free Ti <sub>x</sub> Al <sub>y</sub> Alloy Contact on Non-Recessed i-AlGaIn/GaN. IEEE Electron Device Letters, 2020, 41, 143-146.	3.9	24
6	Very-Low Resistance Contact to 2D Electron Gas by Annealing Induced Penetration Without Spikes Using TaAl/Au on Non-Recessed i-AlGaIn/GaN. IEEE Electron Device Letters, 2020, 41, 1484-1487.	3.9	5
7	Performance Improvement by Blanket Boron Implant in the Sigma-Shaped Trench Before the Embedded SiGe Source/Drain Formation for 28-nm PMOSFET. IEEE Electron Device Letters, 2020, 41, 796-799.	3.9	0
8	Effective Contact Resistivity Reduction for Mo/Pd/n-In <sub>0.53</sub> Ga <sub>0.47</sub> as Contact. IEEE Electron Device Letters, 2019, 40, 1800-1803.	3.9	2
9	Performance Improvement by Cold Xe Pre-Amorphization Implant for Nickel Silicidation of 28-nm PMOSFET. IEEE Electron Device Letters, 2019, 40, 777-779.	3.9	4
10	A Novel One-Transistor Active Pixel Sensor With <i>In-Situ</i> Photoelectron Sensing in 22 nm FD-SOI Technology. IEEE Electron Device Letters, 2019, 40, 738-741.	3.9	23
11	Oxygen Gettering Cap to Scavenge Parasitic Oxide Interlayer in TiSi Contacts. IEEE Electron Device Letters, 2019, 40, 1712-1715.	3.9	1
12	Thermal Stability of TiN/Ti/p <sup>+</sup> -Si <sub>0.3</sub> Ge <sub>0.7</sub> Contact With Ultralow Contact Resistivity. IEEE Electron Device Letters, 2018, 39, 83-86.	3.9	8
13	Improved Ohmic Performance by the Metallic Bilayer Contact Stack of Oxygen-Incorporated La/Ultrathin TiSi<sub>2</sub> on n-Si. IEEE Transactions on Electron Devices, 2018, 65, 1869-1872.	3.0	6
14	Significant Threshold Voltage Shift Induced by Ge Penetration into PMOSFET Channel of 28 nm SRAM. IEEE Electron Device Letters, 2018, , 1-1.	3.9	0
15	KrF Photoresist Profile Modulation by NH <sub>3</sub> Plasma Treatment for 28 nm SRAM. IEEE Transactions on Semiconductor Manufacturing, 2018, 31, 266-269.	1.7	2
16	TiSi(Ge) Contacts Formed at Low Temperature Achieving Around $2\text{ }\mu\text{m}^2\text{-}\Omega\text{cm}^2$ Contact Resistivities to p-SiGe. IEEE Transactions on Electron Devices, 2017, 64, 500-506.	3.0	31
17	Lanthanum and Lanthanum Silicide Contacts on N-Type Silicon. IEEE Electron Device Letters, 2017, 38, 843-846.	3.9	28
18	Optimization of Ni(Pt)/Si-cap/SiGe Silicidation for pMOS Source/Drain Contact. IEEE Transactions on Electron Devices, 2017, 64, 2067-2071.	3.0	2

#	ARTICLE	IF	CITATIONS
19	Thermal Stability Improvement Induced by Laser Annealing for 50-Å... Ni(Pt) Film Silicidation. IEEE Transactions on Electron Devices, 2016, 63, 751-754.	3.0	1
20	Effective Schottky Barrier Height Lowering by TiN Capping Layer for TiSi <sub>2</sub> /Si Power Diode. IEEE Electron Device Letters, 2015, 36, 597-599.	3.9	8
21	Investigation of Ni(Pt)/Si-cap/SiGe solid phase reaction. , 2014, , .		1